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# **APPENDICS**

## APPENDIX A

### 2 Proportion Test for Defect Comparison

This test is interval estimation of 2 populations that are both normal distribution shape. The span of interval was estimated from  $\pm 1.96$  SE (standard error) that cover 95% confidence interval (equal 99.73% of area under curve). Objective of testing is to verify significant difference of two independent data sets.

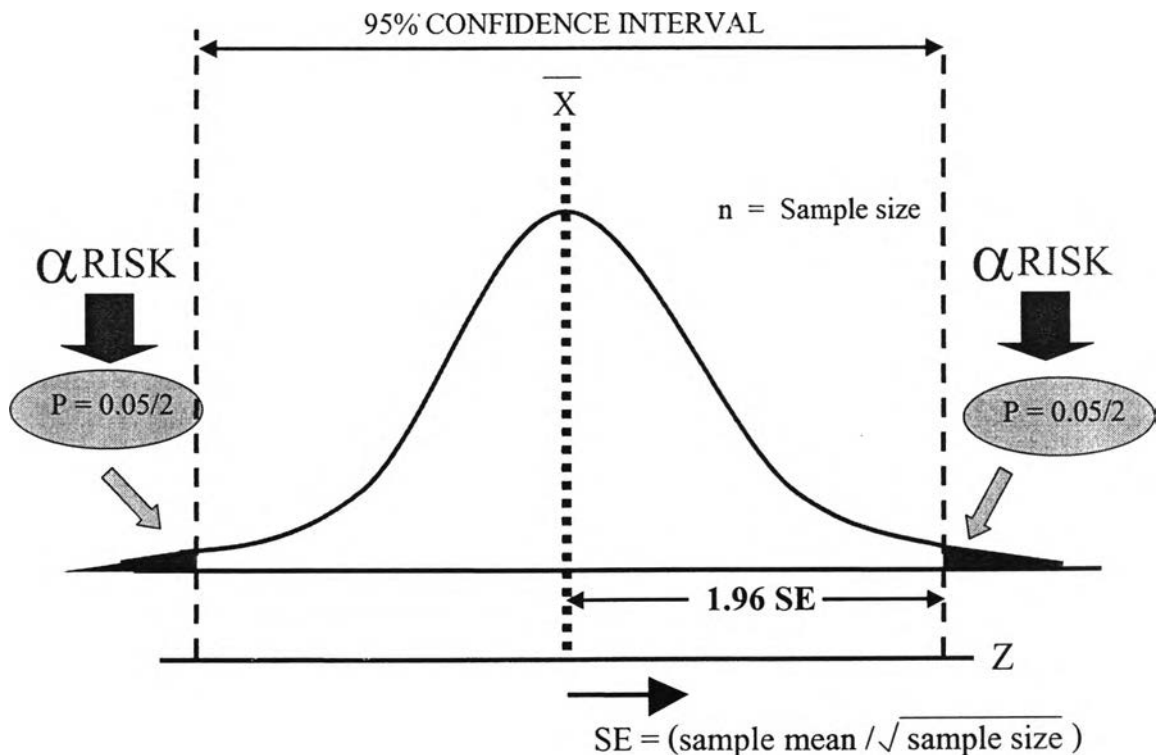


Figure A.1 95% Confidence interval of Z-distribution

The overlap area between these 2 populations would justify potential of probability whether there are similar or difference. If the overlap area is less than 5% of whole distribution will be considered they are significantly different, other than that we would justify that they are from the same population. This significance level is indicated as p-value.

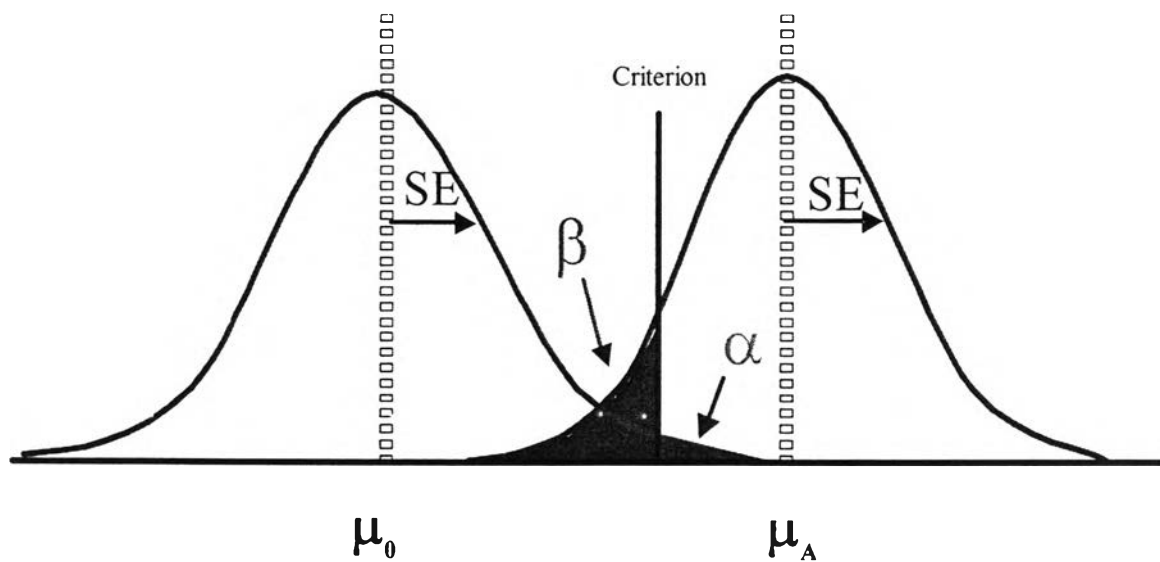
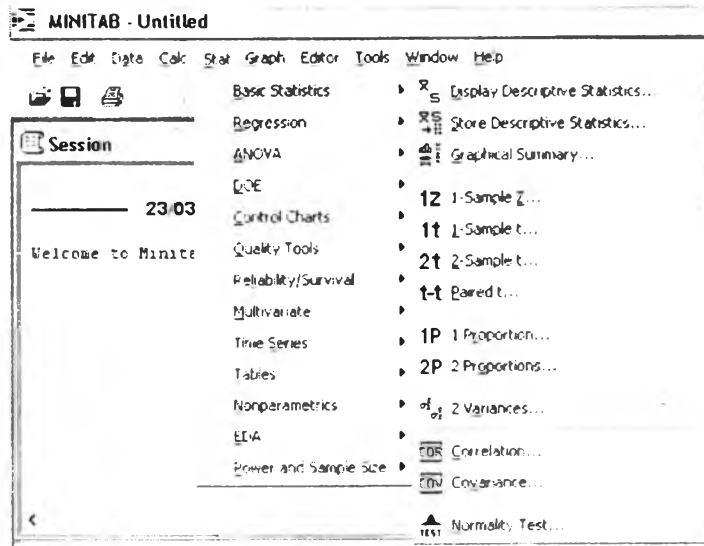


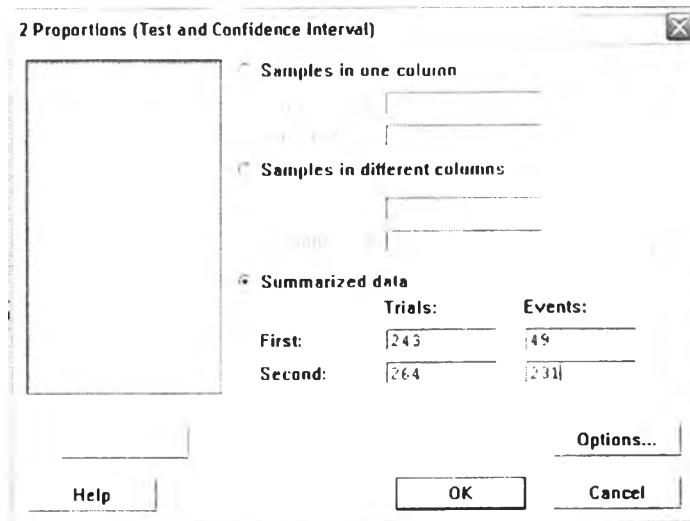
Figure A.2 Overlap area under curve of 2 populations

## 2 Proportion Test by Minitab

Open Minitab program and go to Stat >> Basic Statistics >> 2 Proportions.



Choose 'Summarized data' button in 2 Proportions (Test and Confidence Interval). Key sample size in 'Trials' and defect quantity in 'Events' then click OK.



The analyzed data will show in session window. P-value in this session is the overlap area that indicates the difference of both populations. As below example can be concluded that there is a significant difference between sample no.1 & 2 or the defect of sample no.1 is significantly lower than sample no.2.

Session			
Test and CI for Two Proportions			
Sample	X	N	Sample p
1	49	243	0.201646
2	231	264	0.875000

Difference = p (1) - p (2)  
Estimate for difference: -0.673354  
95% CI for difference: (-0.737669, -0.609039)  
Test for difference = 0 (vs not = 0): Z = -20.52 P-Value = 0.000

## VITA

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